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Invigilator's Signature :	

## CS/M.Tech(ECE)/SEM-1/MCE-104/2012-13 2012

## ADVANCED MICROWAVE COMMUNICATION ENGINEERING

Time Allotted: 3 Hours Full Marks: 70

The figures in the margin indicate full marks.

Candidates are required to give their answers in their own words as far as practicable.

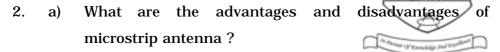
Answer any *five* questions.  $5 \times 14 = 70$ 

- 1. a) Explain why an isolator is located after an unknown genertor.
  - b) Why *H*, *Y* or *Z* are not used to analyze the microwave circuits?
  - c) Why GaAs is used for high frequency and high speed devices?
  - d) What are the limitations of microwave vacuum tubes?
  - e) What is the range of dielectric constant and length of the patch used in microstrip antenna?

3 + 3 + 3 + 3 + 2

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- b) What are the different types of feeding techniques used in microstrip antenna? Discuss one of them.
- c) Design a rectangular microstrip antenna using a substrate (RT/duroid 5880) with dielectric constant of 2.2, h = 0.1588 cm (0.0625 inches) so as to resonate at 10 GHz. 3 + (2 + 3) + 6
- a) Explain how tunnelling action takes place in a tunnel diode.
  - b) Prove that the input impedance of a tunnel diode is given by the expression

$$Z_{in} = R_s + j\omega L_s - [R(j/\omega C) / \{R + (j/\omega C)\}]$$

c) A tunnel diode has the following characteristics :

Negative resistance (R) = 26  $\Omega$ , Series Resistance ( $R_s$ ) =  $1\Omega$ 

Junction capacitance (C) = 5 pF

Now calculate the resistive cut-off frequency. 4 + 6 + 4

- 4. a) Define and prove the properties of S-parameters.
  - b) Prove that for a reciprocal three-port network, the ports cannot all be perfectly matched when the network is dissipationless.
  - c) Show that how a microwave circulator can be used as a reflection type microwave amplifier. 5 + 5 + 4

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- 5. a) What is the meaning of Transferred electron effect?

  Give the sketch of V-I characteristics of a Gunn-diode indicating its threshold point and its implication in operation.
  - b) Explain the operation of a Gunn diode oscillator with suitable circuit diagram.
  - c) The drift velocity of eletron is 2  $\times$  10  $^7$  cm/sec through the active region of length 10  $\times$  10  $^{-4}$  cm. Calculate the natural frequency of the diode and the critical voltage for GaAs. Critical field for GaAs is 3.2 kV/cm.

(3+3)+4+4

- 6. a) What is the purpose of using array of antennas?
  - b) Derive an expression of 'array factor' for N numbers of identical antennas. What are the conditions to obtain linear Broad Side array radiation pattern?
  - c) Describe the Hansen and Woodyard's condition to obtain increased directivity. 2 + (5 + 3) + 4
- a) Discuss the theory of reflection of radio waves from the ionosphere layer.
  - b) What do you mean by critical frequency of the layer?

    Derive the Secant law related to Maximum Usable

    Frequency (MUF).

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- c) Assume that reflection takes place at a height of 400 km and that the maximum density in the ionosphere corresponds to a 0.9 refractive index at 10 MHz. What will be the range ( assume earth is flat ) for which the MUF is 10 MHz? 4 + (2 + 4) + 4
- 8. Write short notes on any *two* of the following: 7 + 7

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- a) IMPATT
- b) Microstrip antenna
- c) Sky wave propagation
- d) Duct propagation.

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